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inner peripheral edge forming said concave portion, and a side of said portion of said lower electrode layer, a side of said ferroelectric layer and a side of said upper electrode layer are flush with each other.

2. (Amended) A ferroelectric memory [according to claim 1], [further] comprising:

an insulation film having a hollow at a top surface; and
a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said hollow, wherein said laminated body includes a lower electrode layer, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer; and the memory further comprising a film formed in a bottom of said hollow and separating between said insulation film and said lower electrode layer.

3. (Twice Amended) A ferroelectric memory [according to claim 1], comprising:

an insulation film having a hollow at a top surface; and
a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said hollow, wherein said laminated body includes a lower electrode layer, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer, and [wherein] said lower electrode layer includes a first electrode portion formed at a corner of said hollow and a second electrode portion formed on said first electrode portion.

4. (Twice Amended) A ferroelectric memory [according to claim 1, wherein said lower electrode is formed on a surface thereof with thin film of a same material

comprising:

an insulation film having a concave portion at a top surface; and

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a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said concave portion, wherein said laminated body includes a lower electrode layer which is brought into contact with a bottom surface of said concave portion, thin film of a same material as that of said lower electrode layer formed on a surface of said lower electrode layer, a ferroelectric layer formed on said thin film and an upper electrode layer formed on said ferroelectric layer, and a side of said thin film, a side of said ferroelectric layer and a side of said upper electrode layer are flush with each other.

5. (Twice Amended) A ferroelectric memory [according to claim 1, wherein], comprising:

an insulation film having a concave portion at a top surface; and
a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said concave portion, wherein said laminated body includes a lower electrode layer which is brought into contact with a bottom surface of said concave portion, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer, wherein said lower electrode layer and said insulation film at respective top surfaces are planarized flush with each other, and a side of said ferroelectric layer and a side of said upper electrode layer are flush with each other.

Respectfully submitted,

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